



AUTOMOTIVE COMPLIANT 4-BIT BIDIRECTIONAL LEVEL TRANSLATOR OPEN-DRAIN AND PUSH-PULL APPLICATIONS

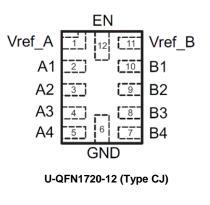
## Description

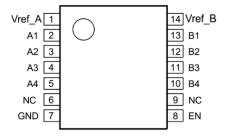
The LSF0204Q is an automotive 4-channel bidirectional multi-voltage level translator for open-drain and push-pull applications. This device is a universal level translator with A port operating from 0.8V to 4.5V (Vref\_A) and B port from 1.8V to 5.5V (Vref\_B). This range allows for bidirectional voltage translations between 0.8V and 5.0V. Be aware that Vref\_B is recommended to be at 1.0V higher than Vref\_A for the best signal integrity.

The EN pin is used to activate the device. When EN is HIGH, the translator switch is on. Otherwise, if EN is LOW, the translator switch is off, and a high-impedance state exists between ports. The EN input circuit is designed to be supplied by Vref\_A. EN must be LOW to ensure the high-impedance state during power-up or power-down to avoid misoperation.

Please note that an external Rpu (pullup resistor) is required on port A and B for push-pull and open-drain application because a pull-high state can avoid misoperation during the power sequence. About the Rpu, the smaller value can result in the larger driving current. Overall, the LSF0204Q is designed for easy-to-use with auto direction. So, there is no need for a direction pin to minimize system effort. This device supports 5V tolerant I/O pins for compatibility with TTL levels in a variety of applications which require a proper voltage translation.

### **Pin Assignments**





TSSOP-14

## Features

- External Rpu (Pullup Resistor) to Set Driving Current in Both Push-Pull and Open-Drain Applications
- Up & Down Translation
  - $\leq$  100MHz; C<sub>L</sub> = 15pF, 30pF
  - ≤ 50MHz; C<sub>L</sub> = 50pF
- Bidirectional Voltage Level Translation Between:
  - 0.8V and 1.8V, 2.5V, 3.3V and 5.0V
  - 1.2V and 1.8V, 2.5V, 3.3V and 5.0V
  - 1.8V and 2.5V, 3.3V and 5.0V
  - 2.5V and 3.3V and 5.0V
  - 3.3V and 5.0V
- ESD Protection Exceeds JESD 22
  - 2000V HBM (A114)
  - 1000V CDM (C101)
- Latchup Exceeds 100mA per JESD 17
- AEC-Q100 Grade 1 Specified from -40°C to +125°C
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The LSF0204Q is suitable for automotive applications requiring specific change control; this part is AEC-Q100 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

## Applications

- GPIO, MDIO, SDIO, SVID, UART
- PMBus<sup>™</sup>, SMBus<sup>™</sup>, I2C, and other interfaces
- Digital infotainment clusters
- Advanced driver assistance systems (ADAS)
- High-performance vehicle computing vision
- HEV/EV battery management systems

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

<sup>2.</sup> See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.



# **Pin Descriptions**

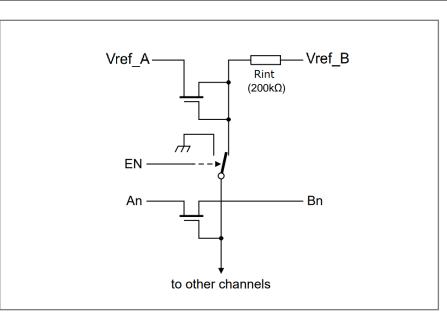
Pin Name	TSSOP-14	U-QFN1720-12 (Type CJ)	Function
V <sub>ref_</sub> A	1	1	Reference supply voltage; A port
A1	2	2	Input/output 1
A2	3	3	Input/output 2
A3	4	4	Input/output 3
A4	5	5	Input/output 4
NC	6	—	No connection. Not internally connected.
GND	7	6	Ground
EN	8	12	Switch enable input; EN is high-active.
NC	9	_	No connection. Not internally connected.
B4	10	7	Input/output 4
B3	11	8	Input/output 3
B2	12	9	Input/output 2
B1	13	10	Input/output 1
V <sub>ref_B</sub>	14	11	Reference supply voltage; B port

# Absolute Maximum Ratings (Note 4)

Symbol	Parameter	Rating	Unit
ESD HBM	Human Body Model ESD Protection	±2	kV
ESD CDM	Charged Device Model ESD Protection	±1	kV
Vref	Supply Reference Voltage Range	-0.5 to +6.0	V
VI	Input Voltage Range	-0.5 to +6.0	V
Vo	Voltage Range Applied to Any Output in the High-Z or Power-Off State	-0.5 to +6.0	V
Існ	Continuous Channel Current	128	mA
Ік	Input Clamp Current, VI < 0	-50	mA
TJ	Operating Junction Temperature	-40 to +150	°C
Tstg	Storage Temperature	-65 to +150	°C

Note: 4. Stresses greater than those listed under Absolute Maximum Ratings can cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to Absolute Maximum Ratings for extended periods can affect device reliability.

## **Functional Diagram**





# Recommended Operating Conditions (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Symbol	Parameter	Min	Max	Unit
V <sub>REF</sub>	Reference Voltage, A & B Ports	0.8	5.5	V
Vi/o	Input/Output Voltage	0.8	5.5	V
Ven	Enable Voltage	0	5.5	V
IPASS	Pass Transistor Current		64	mA
T <sub>A</sub>	Operating Free-Air Temperature	-40	+125	°C

### Electrical Characteristics (Note 5) (@TA = +40°C to +125°C, unless otherwise specified.)

Symbol	Parameter	۲ – L	Test Conditions	Min	Тур	Max	Unit
V <sub>ref_A</sub>	A Port Supply Voltage	—		0.8	_	4.5	V
V <sub>ref_B</sub>	B Port Supply Voltage	—		1.8	_	5.5	V
V <sub>IK</sub>	—	$I_I = -18mA, V_{EN} = 0$		-1.2	_		V
I <sub>IH</sub>	—	$V_{I} = 5V, V_{EN} = 0$		—	_	5.0	μA
I <sub>CCBA</sub>	Leakage from Vref_B to Vref_A	$V_{ref_B} = 3.3V, V_{ref_A} = V_I = 3.3V$ or GND	= 1.8V, $V_{EN} = V_{ref_A}$ , $I_O = 0$	—	_	3.5	μA
I <sub>CCA</sub> + I <sub>CCB</sub>	Total Current Through GND	$V_{ref_B} = 3.3V, V_{ref_A} = V_I = 3.3V \text{ or } GND$	= 1.8V, $V_{EN} = V_{ref_A}$ , $I_O = 0$	_	0.2	—	μA
I <sub>IN</sub>	Control Pin Current	Vref_B = 5.5V, Vref_A	= 4.5V, $V_{EN}$ = 0 to $V_{ref_A}$ , $I_O$ = 0	—	—	±1	μA
l <sub>off</sub>	Power Off Leakage Current	$V_{ref_B} = V_{ref_A} = 0, V_E$	$E_N = GND, I_O = 0, V_I = 5V \text{ or } GND$	—	_	±1	μA
$C_{I}$ (ref_A/B/EN)	—	$V_I = 3V \text{ or } 0$		—	7		pF
C <sub>io (off)</sub>	—	$V_0 = 3V \text{ or } 0, V_{EN} =$	0	-	5.0	6.0	pF
C <sub>io (on)</sub>	—	$V_{O} = 3V \text{ or } 0, V_{EN} =$	V <sub>ref_A</sub>	—	10.5	13	pF
V <sub>IH</sub> (EN)	High-Level Input Voltage	V <sub>ref_A</sub> = 1.5V to 4.5V	1	0.7×V <sub>ref_A</sub>	_	—	V
V <sub>IL (EN)</sub>	Low-Level Input Voltage	V <sub>ref_A</sub> = 1.5V to 4.5V	1	—	_	0.3×Vref_A	V
V <sub>IH</sub> (EN)	High-Level Input Voltage	V <sub>ref_A</sub> = 1.0V to 1.5V	1	0.8×V <sub>ref_A</sub>	_	_	V
V <sub>IL</sub> (EN)	Low-Level Input Voltage	V <sub>ref_A</sub> = 1.0V to 1.5V	1	_	_	0.3×V <sub>ref_A</sub>	V
∆t/∆v (EN)	Input Transition Rise or Fall Rate for EN Pin	_		_	10	_	ns/V
		VI = 0, Io = 64mA	$V_{ref\_A} = V_{EN} = 3.3V$ ; $V_{ref\_B} = 5V$	—	3		Ω
		$V_1 = 0, 10 = 0411A$	$V_{ref\_A} = V_{EN} = 1.8V$ ; $V_{ref\_B} = 5V$	—	4		12
		VI = 0, Io = 32mA	$V_{ref\_A} = V_{EN} = 1.0V$ ; $V_{ref\_B} = 5V$	_	5		Ω
		$V_1 = 0, 10 = 32111A$	$V_{ref\_A} = V_{EN} = 1.8V; V_{ref\_B} = 5V$	—	4		12
R <sub>on</sub>	_	VI = 0, Io = 32mA, Vr	$ef_A = V_{EN} = 2.5V; V_{ref_B} = 5V$	_	3	—	Ω
		VI = 1.8V, Io = 15m	A, $V_{ref_A} = V_{EN} = 3.3V$ ; $V_{ref_B} = 5V$	—	5	—	Ω
		$V_{I} = 1.0V, I_{O} = 10m.$ $V_{ref_B} = 3.3V$	A, $V_{ref_A} = V_{EN} = 1.8V$	_	8	_	Ω
		VI = 0, Io = 10mA, \	/ <sub>ref_A</sub> = V <sub>EN</sub> = 1.0V; V <sub>ref_B</sub> = 3.3V	—	6	—	Ω
		$V_{I} = 0, I_{O} = 10 \text{mA}, V_{O}$	$V_{ref_A} = V_{EN} = 1.0V; V_{ref_B} = 1.8V$	_	6	_	Ω

Note: 5. All typical values are at T<sub>A</sub> = +25°C. Measured by the voltage drop between the A and B terminals at the indicated current through the switch. On-state resistance is determined by the lowest voltage of the two (A or B) terminals. The actual supply current for LSF0204Q is I<sub>CCA</sub> + I<sub>CCB</sub>; the leakage from Vref\_B to Vref\_A can be measured on Vref\_A and Vref\_B pins.



# EN Pin Characteristics (Note 6) (@T<sub>A</sub> = +40°C to +125°C, unless otherwise specified.)

### Translating Down, 3.3V to 1.8V

Parameter	From EN Pin		C∟ = 50pF		C∟ = 30pF		C∟ = 15pF		Unit
Farameter			Тур	Max	Тур	Max	Тур	Max	Unit
t <sub>PLZ</sub> (LOW to OFF)		To Port A or B	13	20	12	20	11	20	ns
t <sub>PZL</sub> (OFF to LOW)			35	50	30	40	25	40	ns
Test Conditions: Vr otherwise noted, s		= 3.3V, V <sub>M</sub> = 0.9V, V	′ <sub>EN</sub> = 1.8V, V	'EXT = Vref_A,	Rpu = NA, V	ιн = 3.3V, Vιι	_ = 0, PRR =	10MHz (unle	SS

#### Translating Up, 1.8V to 3.3V

Parameter			CL =	C∟ = 50pF		30pF	CL =	15pF	Unit
Farameter			Тур	Max	Тур	Max	Тур	Max	Unit
t <sub>PLZ</sub> (LOW to OFF)	From EN Pin	To Port A or B	13	20	12	20	11	20	ns
t <sub>PZL</sub> (OFF to LOW)			35	50	30	40	25	40	ns
Test Conditions: Vr otherwise noted, s	<sub>ref_A</sub> = 1.8V, V <sub>ref_B</sub> = see Figure 1)	: 3.3V, V <sub>M</sub> = 0.9V, V	/ <sub>EN</sub> = 1.8V, V	EXT = Vref_A,	Rpu = NA, V	′ін = 3.3V, Vil	= 0, PRR =	10MHz (unle	SS

### Translating Down Characteristics (Note 6) (@T<sub>A</sub> = +40°C to +125°C, unless otherwise specified.)

#### Translating Down, 5.0V to 1.8V

Deremeter			C <sub>L</sub> = 50pF		C <sub>L</sub> = 30pF		C <sub>L</sub> =	15pF	Unit	
Parameter	From (Input)	To (Output)	Тур	Max	Тур	Max	Тур	Max	Unit	
t <sub>PLH</sub>			0.6	5.1	0.5	5.1	0.3	5.0	ns	
t <sub>PHL</sub>	В	А	1.1	4.8	0.9	4.5	0.5	4.4	ns	
f <sub>MAX</sub>			ţ	50	1	00	1	00	MHz	
	ref_A = 1.8V, Vref_B =	5.0V, V <sub>M</sub> = 2.15V,					= 10MHz (ur	nless otherwi		

#### Translating Down, 3.3V to 1.8V

Parameter	From (Input)		C∟ =	50pF	CL =	30pF	CL =	15pF	Unit
Farameter	From (input)	To (Output)	Тур	Max	Тур	Max	Тур	Max	Unit
t <sub>PLH</sub>			0.7	5.5	0.5	5.3	0.3	5.2	ns
t <sub>PHL</sub>	В	А	0.9	4.9	0.7	4.7	0.5	4.5	ns
f <sub>MAX</sub>			Ę	50	1	00	1	00	MHz
Test Conditions: V see Figure 1)	<sub>ref_A</sub> = 1.8V, V <sub>ref_B</sub> =	: 3.3V, V <sub>M</sub> = 1.15V,	V <sub>EN</sub> = 1.8V,	Switch = S2,	V <sub>IH</sub> = 3.3V, '	V <sub>IL</sub> = 0, PRR	= 10MHz (ur	nless otherwis	se noted,

#### Translating Down, 3.3V to 1.2V

Parameter	From (Input)	To (Output)	C∟ = 50pF		C∟ = 30pF		CL =	Unit	
Farameter	From (input)	To (Output)	Тур	Max	Тур	Max	Тур	Max	Unit
t <sub>PLH</sub>			0.8	4.1	0.5	3.9	0.3	3.8	ns
t <sub>PHL</sub>	В	А	0.9	4.7	0.7	4.5	0.6	4.3	ns
f <sub>MAX</sub>			5	50	1	00	1	00	MHz
Test Conditions: Vi see Figure 1)	ref_A = 1.2V, Vref_B =	= 3.3V, V <sub>M</sub> = 0.85V,	VEN = 1.2V,	Switch = S2,	VIH = 3.3V,	VIL = 0, PRR	= 10MHz (ur	nless otherwi	se noted,

Note: 6. All typical values are measured at T<sub>A</sub> = +25°C. Logic levels: V<sub>OL</sub> and V<sub>OH</sub> are typical output voltage levels that occur with the output load. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10MHz; Z<sub>O</sub> = 50Ω. Definitions test circuit: C<sub>L</sub> = Load capacitance including jig and probe capacitance; Rpu = pullup resistor as load resistance; S1/S2 = Test selection switch.



### Translating Down Characteristics (continued) (Note 6) (@TA = +40°C to +125°C, unless otherwise specified.)

#### Translating Down, 1.8V to 1.2V

Parameter	From (Input)		CL =	50pF	CL =	30pF	CL =	15pF	Unit
Farameter	From (input)	To (Output)	Тур	Max	Тур	Max	Тур	Max	Unit
t <sub>PLH</sub>			1.3	4.6	1.1	4.4	1.0	4.1	ns
t <sub>PHL</sub>	В	А	1.4	5.3	1.3	5.1	1.2	4.7	ns
f <sub>MAX</sub>			Ę	50	1	00	1	00	MHz
	ref_A = 1.2V, Vref_B =	1.8V, V <sub>M</sub> = 0.65V,	V <sub>EN</sub> = 1.2V,	Switch = S2,	VIH = 1.8V,	VIL = 0, PRR	= 10MHz (ur	nless otherwi	se noted

#### Translating Down, 1.8V to 0.8V

Parameter	From (Input)	To (Output)	CL =	50pF	C∟ = 30pF		CL =	Unit	
Farameter	From (input)	To (Output)	Тур	Max	Тур	Max	Тур	Max	Unit
t <sub>PLH</sub>			1.5	4.7	1.2	4.5	1.1	4.3	ns
t <sub>PHL</sub>	В	А	1.7	5.6	1.6	5.3	1.3	5.0	ns
f <sub>MAX</sub>			Ę	50	8	30	1	00	MHz
Test Conditions: V <sub>r</sub> see Figure 1)	$ref_A = 0.8V, V_{ref_B} =$	1.8V, V <sub>M</sub> = 0.55V,	$V_{EN} = 0.8V,$	Switch = S2,	V <sub>IH</sub> = 1.8V,	V <sub>IL</sub> = 0, PRR	= 10MHz (ui	nless otherwi	se noted,

### Translating Up Characteristics (Note 6) (@T<sub>A</sub> = +40°C to +125°C, unless otherwise specified.)

#### Translating Up, 1.8V to 5.0V

Parameter	From (Input)	m (Input) To (Output)	C∟ = 50pF		C∟ = 30pF		C∟ = 15pF		Unit
Farameter	From (input)	To (Output)	Тур	Max	Тур	Max	Тур	Max	Unit
t <sub>PLH</sub>			0.6	5.7	0.4	5.3	0.2	5.2	ns
t <sub>PHL</sub>	A	В	1.3	6.7	1.0	6.4	0.7	5.3	ns
f <sub>MAX</sub>			5	50	1	00	1	00	MHz
	ref_A = 1.8V, Vref_B = noted, see Figure 2		V <sub>EN</sub> = 1.8V,	Switch = S1,	Rpu = 500Ω	9, V <sub>EXT</sub> = 5.0\	/, V <sub>IH</sub> = 1.8V,	$V_{IL} = 0$ , PRF	R = 10MHz

#### Translating Up, 1.8V to 3.3V

Parameter	From (Innut)		C <sub>L</sub> =	50pF	C <sub>L</sub> =	30pF	C <sub>L</sub> =	15pF	Unit
Parameter	From (Input)	To (Output)	Тур	Max	Тур	Max	Тур	Max	Unit
t <sub>PLH</sub>			0.6	5.7	0.4	5.3	0.2	5.2	ns
t <sub>PHL</sub>	А	В	1.3	6.7	1.0	6.4	0.7	5.3	ns
f <sub>MAX</sub>			5	50	1	00	1	00	MHz
	MAX 100 <td>R = 10MHz</td>							R = 10MHz	

#### Translating Up, 1.2V to 3.3V

Parameter	From (Input)	To (Output)	CL =	50pF	CL =	30pF	C∟ =	15pF	Unit
Farameter	From (input)	To (Output)	Тур	Max	Тур	Max	Тур	Max	Unit
t <sub>PLH</sub>			0.7	7.3	0.4	7.1	0.2	6.9	ns
t <sub>PHL</sub>	A	В	1.6	7.1	1.3	6.5	1.0	5.4	ns
f <sub>MAX</sub>			5	50	1	00	1	00	MHz
	ref_A = 1.2V, Vref_B =	, , ,	$V_{EN} = 1.2V$ ,	Switch = S1,	Rpu = 500Ω	e, Vext = 3.3∖	/, VIH = 1.2V	, VIL = 0, PRF	R = 10MHz

Note: 6. All typical values are measured at  $T_A = +25^{\circ}$ C. Logic levels:  $V_{OL}$  and  $V_{OH}$  are typical output voltage levels that occur with the output load. All input pulses are supplied by generators having the following characteristics: PRR  $\leq 10$ MHz;  $Z_O = 50\Omega$ . Definitions test circuit:  $C_L$  = Load capacitance including jig and probe capacitance; Rpu = pullup resistor as load resistance; S1/S2 = Test selection switch.



## Translating Up Characteristics (continued) (Note 6) (@TA = +40°C to +125°C, unless otherwise specified.)

#### Translating Up, 1.2V to 1.8V

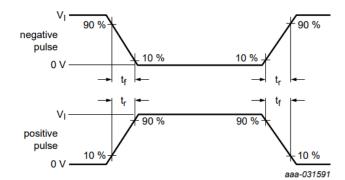
Parameter	From (Input)		CL =	: 50pF	CL =	30pF	CL =	15pF	Unit
Farameter	From (input)	To (Output)	Тур	Max	Тур	Max	Тур	Max	Unit
t <sub>PLH</sub>			0.7	7.3	0.4	7.1	0.2	6.9	ns
t <sub>PHL</sub>	A	В	1.6	7.1	1.3	6.5	1.0	5.4	ns
f <sub>MAX</sub>			Ę	50	1	00	1	00	MHz
	ref_A = 1.2V, Vref_B = noted, see Figure ?		V <sub>EN</sub> = 1.2V,	Switch = S1,	Rpu = 5000	Ω, Vext = 3.3\	/, VIH = 1.2V	, VIL = 0, PRF	R = 10MHz

#### Translating Up, 0.8V to 1.8V

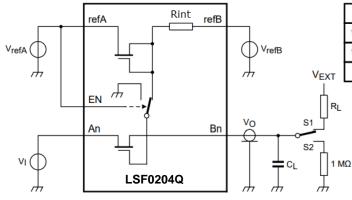
Parameter	From (Input)		CL =	50pF	CL =	30pF	C∟ =	15pF	Unit
Farameter	From (Input)	To (Output)	Тур	Max	Тур	Max	Тур	Max	Unit
t <sub>PLH</sub>			0.7	7.3	0.5	7.2	0.3	6.9	ns
t <sub>PHL</sub>	А	В	1.6	7.1	1.4	6.6	1.0	5.4	ns
f <sub>MAX</sub>			4	0	8	30	1	00	MHz
	$r_{ef_A} = 0.8V, V_{ref_B} = 0.8V$		$V_{EN} = 0.8V,$	Switch = S1,	Rpu = 500Ω	, V <sub>EXT</sub> = 1.8∖	∕, V <sub>IH</sub> = 0.8V	, V <sub>IL</sub> = 0, PRF	R = 10MHz

Note: 6. All typical values are measured at T<sub>A</sub> = +25°C. Logic levels: V<sub>OL</sub> and V<sub>OH</sub> are typical output voltage levels that occur with the output load. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10MHz; Z<sub>O</sub> = 50Ω. Definitions test circuit: C<sub>L</sub> = Load capacitance including jig and probe capacitance; Rpu = pullup resistor as load resistance; S1/S2 = Test selection switch.

### **Parameter Measurement Information**



### V<sub>I</sub> source waveform



Test circuit

switch

**S**1

S2

**S**1

Measurement

tPHL/tPLH, fmax

tPHL/tPLH, fmax

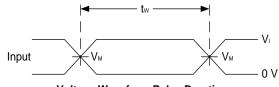
t<sub>PZL</sub>/t<sub>PLZ</sub>

Translating up

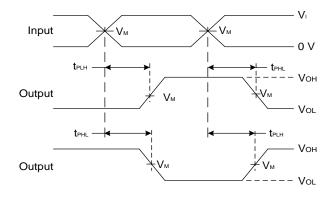
Translating down



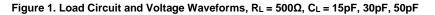
# Parameter Measurement Information (continued)



Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non-Inverting Outputs



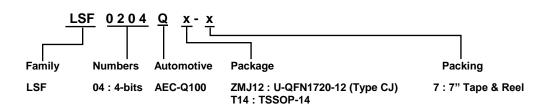
# Package Characteristics

Symbol	Parameter	Package	Test Conditions	Min	Тур	Max	Unit
0	Thermal Resistance	U-QFN1720-12 (Type CJ)	(Note 7)	—	185	—	
θја	Junction-to-Ambient	TSSOP-14 (Note 7)	_	125	_	°C/W	
0	Thermal Resistance	U-QFN1720-12 (Type CJ)	(Note 7)	—	65	_	°C/vv
θις	Junction-to-Case	TSSOP-14	(Note 7)	_	72	—	

Note: 7. Test condition for the package type(s): device mounted on JEDEC standard PCB per JESD51, with minimum recommended pad layout.



### Ordering Information (Notes 8 & 9)



Part Number	Part Number Suffix	Package Code Package		Packing	(Note 10)
Fait Number		Fackage Coue	Package	Qty.	Carrier
LSF0204QZMJ12-7	-7	ZMJ12	U-QFN1720-12 (Type CJ)	3,000	7" Tape and Reel
LSF0204QT14-13	-13	T14	TSSOP-14	2,500	13" Tape and Reel

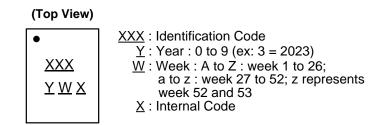
Notes: 8. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

9. Pad layout as shown in Diodes Incorporated's package outline PDFs, which can be found on our website at http://www.diodes.com/packageoutlines.html.

10. The taping orientation is located on our website at https://www.diodes.com/assets/Packaging-Support-Docs/ap02007.pdf.

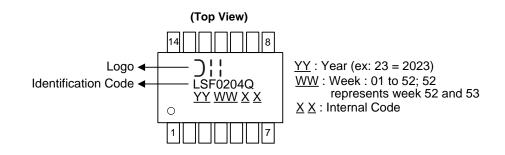
## **Marking Information**

### (1) U-QFN1720-12 (Type CJ)



Part Number	Package	Identification Code
LSF0204QZMJ12-7	U-QFN1720-12 (Type CJ)	J2Q

#### (2) TSSOP-14



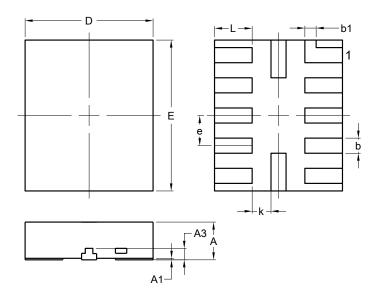
Part Number	Package	Identification Code
LSF0204QT14-13	TSSOP-14	LSF0204Q



# **Package Outline Dimensions**

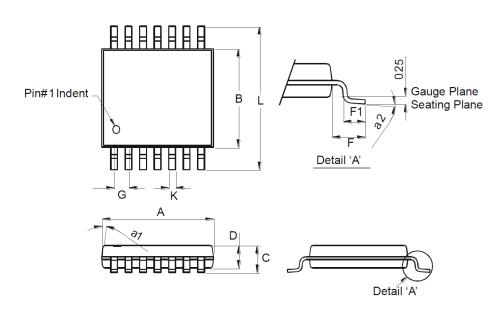
Please see http://www.diodes.com/package-outlines.html for the latest version.

### (1) U-QFN1720-12 (Type CJ)



	U-QFN1720-12 (Type CJ)					
Dim	Min	Max	Тур			
Α	0.450	0.550				
A1	0.00	0.050				
A3	0	0.152 REF				
b	0.150	0.250				
b1	0	.150 RE	F			
D	1.600	1.800				
Е	1.900	2.100				
e	0	.400 BS	C			
k	0	.250 RE	F			
L	0.400	0.600				
All [	Dimens	ions in	mm			

### (2) TSSOP-14



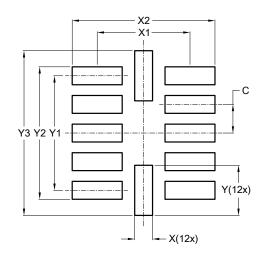
	TSSOP-14					
Dim	Min	Max				
a1	7° (	4X)				
a2	0°	8°				
Α	4.9	5.10				
В	4.30	4.50				
C	-	1.2				
D	0.8	1.05				
F	1.00	Тур				
F1	0.45	0.75				
G	0.65	Тур				
κ	0.19	0.30				
L	6.40	6.40 Typ				
All Dir	mension	s in mm				



# Suggested Pad Layout

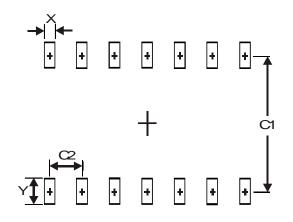
Please see http://www.diodes.com/package-outlines.html for the latest version.

### (1) U-QFN1720-12 (Type CJ)



Dimensions	Value (in mm)
С	0.400
Х	0.250
X1	1.300
X2	2.000
Y	0.700
Y1	1.600
Y2	1.850
Y3	2.300

### (2) TSSOP-14



Dimensions	Value (in mm)
Х	0.45
Y	1.45
C1	5.9
C2	0.65

# **Mechanical Data**

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 🐵
- Max Soldering Temperature +260°C for 30 secs as per JEDEC J-STD-020
- Weight: U-QFN1720-12 (Type CJ) 21.5mg (Approximate) TSSOP-14 – 83.5mg (Approximate)



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